

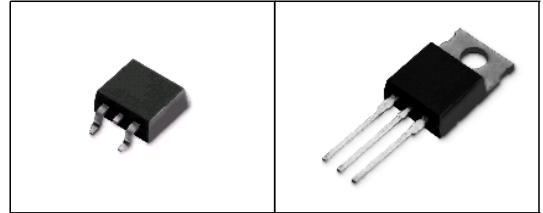
### Silicon Carbide Schottky Diode

- Revolutionary semiconductor material - Silicon Carbide
- Switching behavior benchmark
- No reverse recovery
- No temperature influence on the switching behavior
- No forward recovery

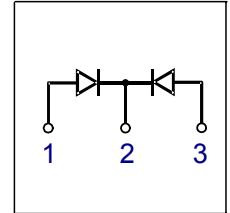
### Product Summary

$V_{RRM}$	300	V
$Q_c$	23	nC
$I_F$	2x10	A

P-T0220-3.SMD P-T0220-3-1.



Type	Package	Ordering Code	Marking
SDP20S30	P-T0220-3-1.	Q67040-S4419	D20S30
SDB20S30	P-T0220-3.SMD	Q67040-S4374	S20S30



**Maximum Ratings**, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified (per leg)

Parameter	Symbol	Value	Unit
Continuous forward current, $T_C=100^\circ\text{C}$	$I_F$	10	A
RMS forward current, $f=50\text{Hz}$	$I_{FRMS}$	14	
Surge non repetitive forward current, sine halfwave $T_C=25^\circ\text{C}$ , $t_p=10\text{ms}$	$I_{FSM}$	36	
Repetitive peak forward current $T_j=150^\circ\text{C}$ , $T_C=100^\circ\text{C}$ , $D=0.1$	$I_{FRM}$	45	
Non repetitive peak forward current $t_p=10\mu\text{s}$ , $T_C=25^\circ\text{C}$	$I_{FMAX}$	100	
$i^2t$ value, $T_C=25^\circ\text{C}$ , $t_p=10\text{ms}$	$\int i^2 dt$	6.5	$\text{A}^2\text{s}$
Repetitive peak reverse voltage	$V_{RRM}$	300	V
Surge peak reverse voltage	$V_{RSM}$	300	
Power dissipation, single diode mode, $T_C=25^\circ\text{C}$	$P_{tot}$	65	W
Operating and storage temperature	$T_j$ , $T_{stg}$	-55... +175	$^\circ\text{C}$

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Characteristics</b>					
Thermal resistance, junction - case (per leg)	$R_{thJC}$	-	-	2.3	K/W
SMD version, device on PCB: P-TO263-3-2: @ min. footprint P-TO263-3-2: @ 6 cm <sup>2</sup> cooling area <sup>1)</sup>	$R_{thJA}$	-	-	62	
		-	35	-	

**Electrical Characteristics**, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified (per leg)

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Static Characteristics</b>					
Diode forward voltage $I_F=10\text{A}, T_j=25^\circ\text{C}$ $I_F=10\text{A}, T_j=150^\circ\text{C}$	$V_F$	-	1.5	1.7	V
		-	1.5	1.9	
Reverse current $V_R=300\text{V}, T_j=25^\circ\text{C}$ $V_R=300\text{V}, T_j=150^\circ\text{C}$	$I_R$	-	15	200	$\mu\text{A}$
		-	20	1000	

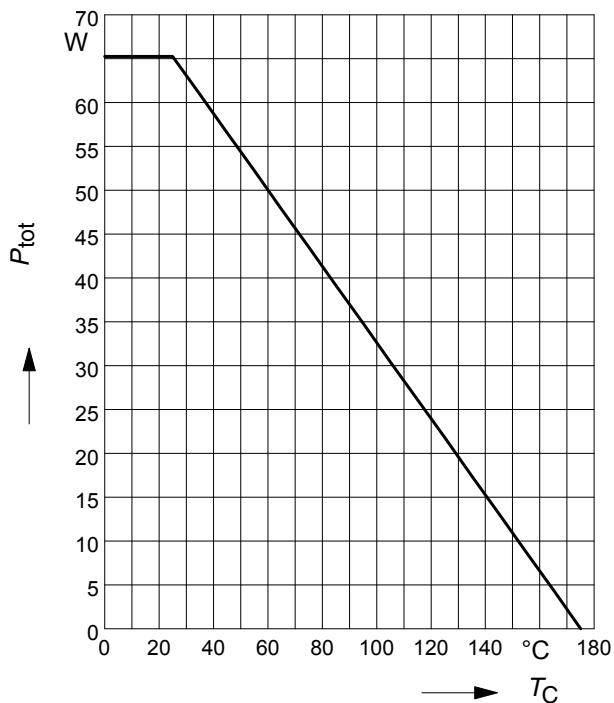
<sup>1)</sup>Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70  $\mu\text{m}$  thick) copper area for drain connection. PCB is vertical without blown air.

**Electrical Characteristics**, at  $T_j = 25^\circ\text{C}$ , unless otherwise specified (per leg)

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>AC Characteristics</b>					
Total capacitive charge <sup>1)</sup> $V_R=200\text{V}, I_F=10\text{A}, di_F/dt=-200\text{A}/\mu\text{s}, T_j=150^\circ\text{C}$	$Q_c$	-	23	-	nC
Switching time <sup>2)</sup> $V_R=200\text{V}, I_F=10\text{A}, di_F/dt=-200\text{A}/\mu\text{s}, T_j=150^\circ\text{C}$	$t_{rr}$	-	n.a.	-	ns
Total capacitance $V_R=0\text{V}, T_C=25^\circ\text{C}, f=1\text{MHz}$ $V_R=150\text{V}, T_C=25^\circ\text{C}, f=1\text{MHz}$ $V_R=300\text{V}, T_C=25^\circ\text{C}, f=1\text{MHz}$	C	-	600	-	pF
		-	55	-	
		-	40	-	

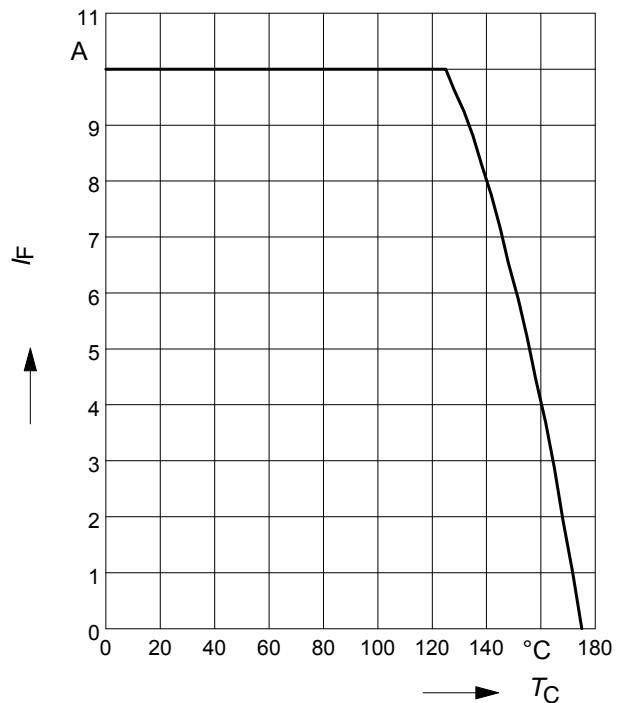
**1 Power dissipation (per leg)**

$$P_{\text{tot}} = f(T_C)$$


**2 Diode forward current (per leg)**

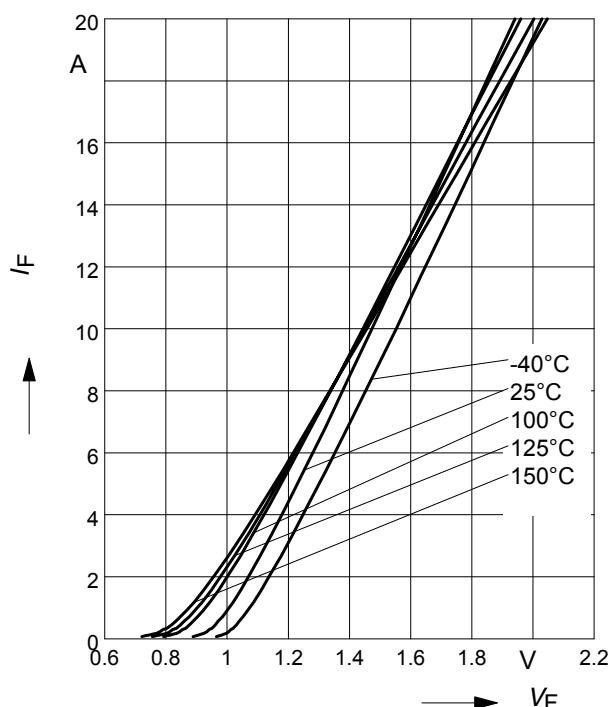
$$I_F = f(T_C)$$

parameter:  $T_J \leq 175$  °C

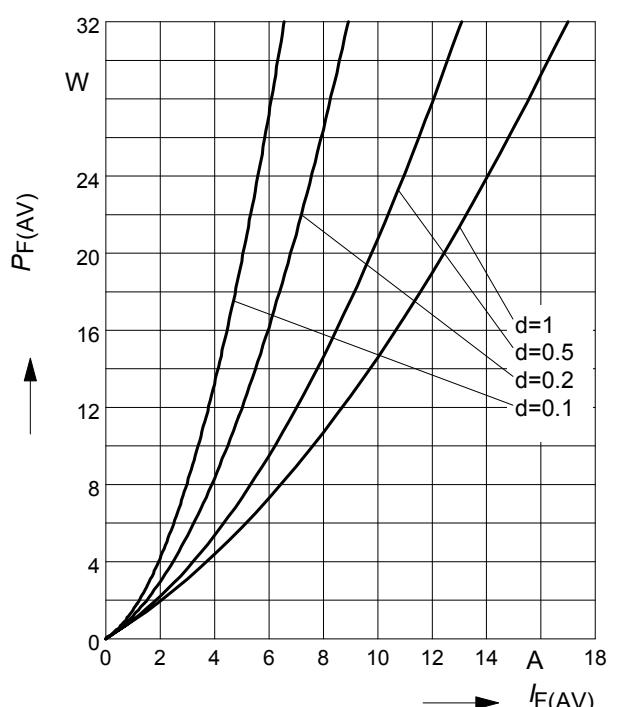

**3 Typ. forward characteristic (per leg)**

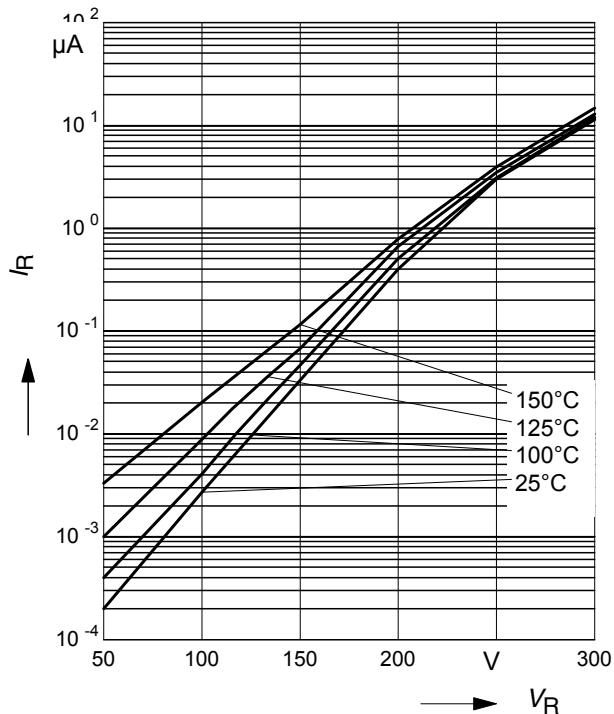
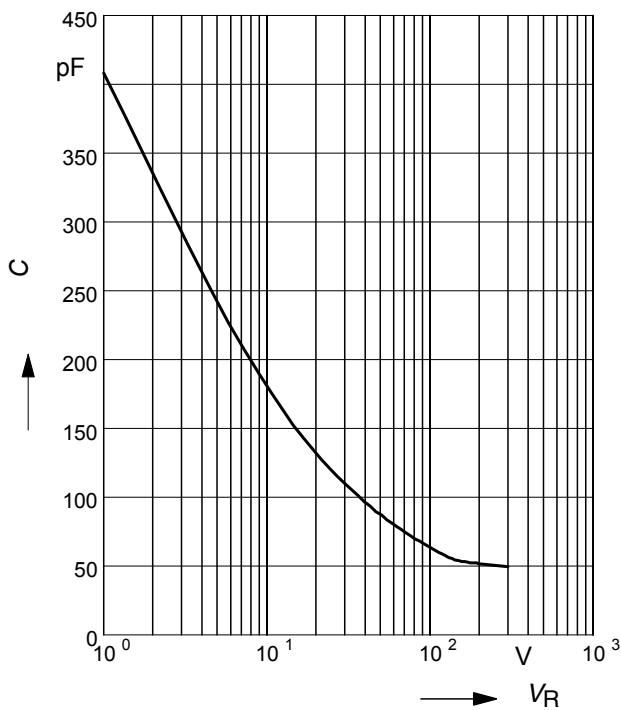
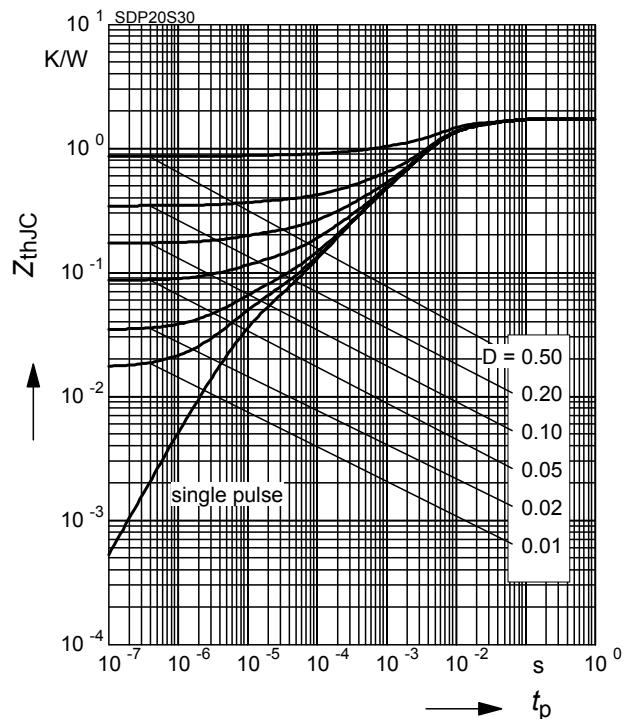
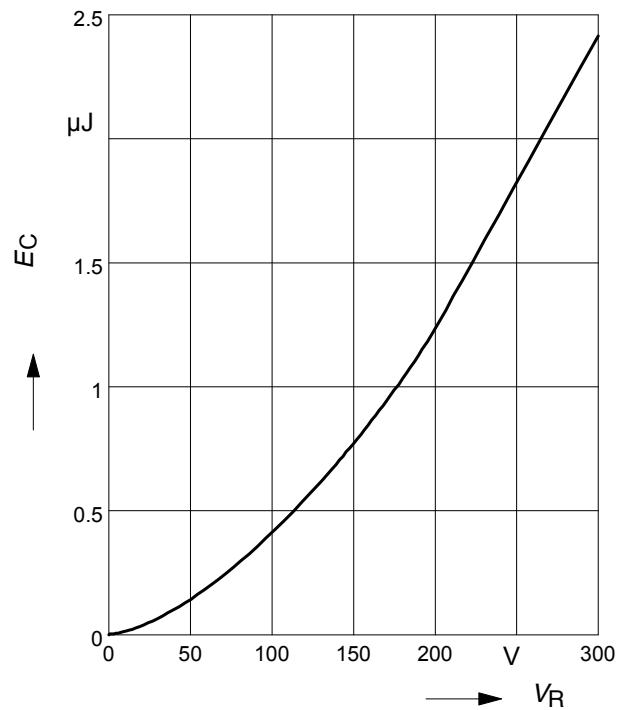
$$I_F = f(V_F)$$

parameter:  $T_J$ ,  $t_p = 350$  µs


**4 Typ. forward power dissipation vs. average forward current (per leg)**

$$P_{F(\text{AV})} = f(I_F) \quad T_C = 100^\circ\text{C}, d = t_p/T$$

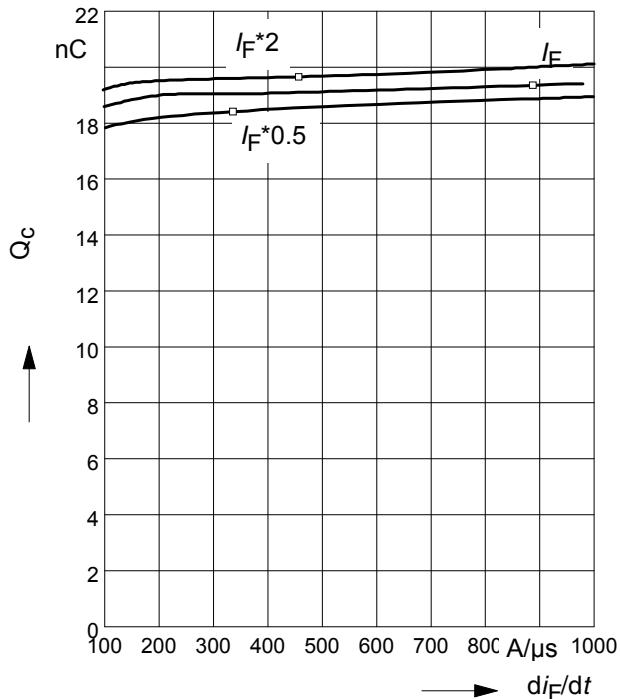


**5 Typ. reverse current vs. reverse voltage  
(per leg)  $I_R = f(V_R)$** 

**7 Typ. capacitance vs. reverse voltage  
(per leg)  $C = f(V_R)$   
parameter:  $T_C = 25^\circ\text{C}$ ,  $f = 1 \text{ MHz}$** 

**6 Transient thermal impedance (per leg)  
 $Z_{\text{thJC}} = f(t_p)$   
parameter :  $D = t_p/T$** 

**8 Typ. C stored energy (per leg)  
 $E_C = f(V_R)$** 


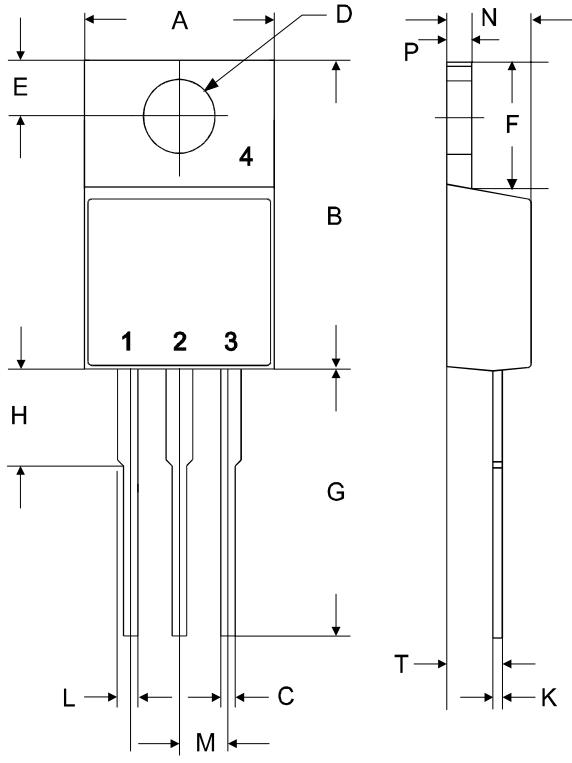
### **9 Typ. capacitive charge vs. current slope**

$$(\text{per leg}) Q_C = f(dI_F/dt)$$

parameter:  $T_J = 150 \text{ }^{\circ}\text{C}$

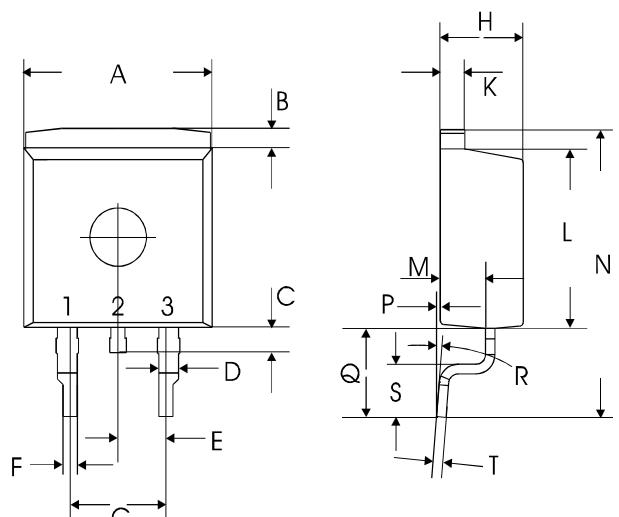


**P-TO220-3-1**



symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	9.70	10.30	0.3819	0.4055
B	14.88	15.95	0.5858	0.6280
C	0.65	0.86	0.0256	0.0339
D	3.55	3.89	0.1398	0.1531
E	2.60	3.00	0.1024	0.1181
F	6.00	6.80	0.2362	0.2677
G	13.00	14.00	0.5118	0.5512
H	4.35	4.75	0.1713	0.1870
K	0.38	0.65	0.0150	0.0256
L	0.95	1.32	0.0374	0.0520
M	2.54 typ.		0.1 typ.	
N	4.30	4.50	0.1693	0.1772
P	1.17	1.40	0.0461	0.0551
T	2.30	2.72	0.0906	0.1071

**TO-220-3-45 (P-TO220SMD)**



symbol	dimensions			
	[mm]		[inch]	
	min	max	min	max
A	9.80	10.00	0.3858	0.3937
B	1.3 typ.		0.0512 typ.	
C	1.25	1.75	0.0492	0.0689
D	0.95	1.15	0.0374	0.0453
E	2.54 typ.		0.1 typ.	
F	0.72	0.85	0.0283	0.0335
G	5.08 typ.		0.2 typ.	
H	4.30	4.50	0.1693	0.1772
K	1.28	1.40	0.0504	0.0551
L	9.00	9.40	0.3543	0.3701
M	2.30	2.50	0.0906	0.0984
N	14.1 typ.		0.5551 typ.	
P	0.00	0.20	0.0000	0.0079
Q	3.30	3.90	0.1299	0.1535
R	8° max		8° max	
S	1.70	2.50	0.0669	0.0984
T	0.50	0.65	0.0197	0.0256
U	10.8 typ.		0.4252 typ.	
V	1.35 typ.		0.0532 typ.	
W	6.43 typ.		0.2532 typ.	
X	4.60 typ.		0.1811 typ.	
Y	9.40 typ.		0.3701 typ.	
Z	16.15 typ.		0.6358 typ.	

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